Hisashi Murakami

List of Publications by Year
in descending order

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143	4,671	26	66
papers	citations	h-index	g-index
		249298	116156

144	144	144	3042
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Vertical Î²-Ga₂O₃ Schottky barrier diodes with trench staircase field plate. Applied Physics Express, 2022, 15, 054001.	1.1	29
2	Effect of substrate orientation on homoepitaxial growth of <i>Î²</i> -Ga2O3 by halide vapor phase epitaxy. Applied Physics Letters, 2022, 120, .	1.5	13
3	Anisotropic complex refractive index of Î²-Ga2O3 bulk and epilayer evaluated by terahertz time-domain spectroscopy. Applied Physics Letters, 2021, 118, .	1.5	45
4	Aperture-limited conduction and its possible mechanism in ion-implanted current aperture vertical <i>Î²</i> -Ga2O3 MOSFETs. Applied Physics Letters, 2021, 118, .	1.5	19
5	Facet stability of GaN during tri-halide vapor phase epitaxy: an ab initio-based approach. CrystEngComm, 2021, 23, 1423-1428.	1.3	0
6	Growth of lattice-relaxed InGaN thick films on patterned sapphire substrates by tri-halide vapor phase epitaxy. Japanese Journal of Applied Physics, 2021, 60, 105501.	0.8	1
7	Terahertz time-domain spectroscopy of wide-bandgap semiconductors GaN and Î²-Ga2O3. , 2021, , .		0
8	Growth of Highly Crystalline GaN at High Growth Rate by Trihalide Vaporâ€Phase Epitaxy. Physica Status Solidi (B): Basic Research, 2020, 257, 1900564.	0.7	4
9	Enhancement-Mode eta -Ga₂O₃ Current Aperture Vertical MOSFETs With N-Ion-Implanted Blocker. IEEE Electron Device Letters, 2020, 41, 296-299.	2.2	65
10	Characterization of trap states in buried nitrogen-implanted <i>Î²</i>-Ga2O3. Applied Physics Letters, 2020, 117, .	1.5	7
11	Hydride vapor phase epitaxy of Si-doped AlN layers using SiCl4 as a doping gas. Journal of Crystal Growth, 2020, 545, 125730.	0.7	3
12	Vertical Gallium Oxide Transistors with Current Aperture Formed Using Nitrogen-Ion Implantation Process. , 2020, , .		2
13	Temperature dependence of Ga2O3 growth by halide vapor phase epitaxy on sapphire and <i>Î²</i> -Ga2O3 substrates. Applied Physics Letters, 2020, 117, .	1.5	11
14	Dislocation density reduction in (101 1) GaN at a high temperature using tri-halide vapor phase epitaxy. , 2020, , .		0
15	Halide Vapor Phase Epitaxy 1. Springer Series in Materials Science, 2020, , 185-202.	0.4	1
16	Charge trapping and degradation of Ga2O3 isolation structures for power electronics. , 2020, , .		0
17	Electrical properties of eta-Ga2O3 homoepitaxial layer measured by terahertz time-domain spectroscopy. , 2020, , .		0
18	Vertical Ga₂O₃ Schottky Barrier Diodes With Guard Ring Formed by Nitrogen-Ion Implantation. IEEE Electron Device Letters, 2019, 40, 1487-1490.	2.2	126

#	Article	IF	Citations
19	GaN growth via tri-halide vapor phase epitaxy using solid source of GaCl₃: investigation of the growth dependence on NH₃ and additional Cl₂. Japanese Journal of Applied Physics, 2019, 58, SC1022.	0.8	4
20	Influence of intermediate layers on thick InGaN growth using tri-halide vapor phase epitaxy. Japanese Journal of Applied Physics, 2019, 58, SC1027.	0.8	3
21	Frontiers of Nitride Semiconductor Research. Japanese Journal of Applied Physics, 2019, 58, SC0001.	0.8	0
22	Growth of GaN on a three-dimensional SCAATTM bulk seed by tri-halide vapor phase epitaxy using GaCl3. Japanese Journal of Applied Physics, 2019, 58, SC1024.	0.8	3
23	Stability and degradation of isolation and surface in Ga2O3 devices. Microelectronics Reliability, 2019, 100-101, 113453.	0.9	6
24	Invited: Process and Characterization of Vertical Ga2O3 Transistors. , 2019, , .		0
25	Enhancement-Mode Current Aperture Vertical Ga₂O₃ MOSFETs. , 2019, , .		2
26	Vapor Phase Epitaxy of (133) and (211) CdTe on (211) Si Substrates Using Metallic Cd Source. Journal of Electronic Materials, 2019, 48, 454-459.	1.0	3
27	Dependence of surface morphology at initial growth of CdTe on the II/VI on (2â€¯1â€¯1) Si substrates by vapor phase epitaxy using metallic Cd source. Journal of Crystal Growth, 2019, 506, 185-189.	0.7	1
28	Current Aperture Vertical <inline-formula> <tex-math notation="LaTeX">eta </tex-math> </inline-formula>-Ga₂O₃ MOSFETs Fabricated by N- and Si-Ion Implantation Doping. IEEE Electron Device Letters, 2019, 40, 431-434.	2.2	135
29	Vertical Ga₂O₃ Schottky Barrier Diodes with Guard Ring Formed by Nitrogen-Ion Implantation. , 2019, , .		3
30	Comparison of O2 and H2O as oxygen source for homoepitaxial growth of Î²-Ga2O3 layers by halide vapor phase epitaxy. Journal of Crystal Growth, 2018, 492, 39-44.	0.7	23
31	Halide vapor phase epitaxy of Si doped Î²-Ga2O3 and its electrical properties. Thin Solid Films, 2018, 666, 182-184.	0.8	146
32	Acceptor doping of <i>Î²</i>-Ga2O3 by Mg and N ion implantations. Applied Physics Letters, 2018, 113, .	1.5	129
33	Growth temperatures and the excess chlorine effect of N-Polar GaN growth via tri-halide vapor phase epitaxy. Journal of Crystal Growth, 2018, 502, 7-13.	0.7	7
34	Recent Advances in Ga2O3 MOSFET Technologies. , 2018, , .		1
35	All-ion-implanted planar-gate current aperture vertical Ga₂O₃ MOSFETs with Mg-doped blocking layer. Applied Physics Express, 2018, 11, 064102.	1.1	73
36	Latest progress in gallium-oxide electronic devices. , 2018, , .		0

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37	Nonpolar m-plane and semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0015.gif" overflow="scroll"><mml:mrow><mml:mo stretchy="false">(</mml:mo><mml:mn>10</mml:mn></mml:mrow><mml:mover) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 747 Td	0.7	6
38	Quasiequilibrium crystal shape and kinetic Wulff plot for GaN grown by trihalide vapor phase epitaxy using GaCl₃. Physica Status Solidi (B): Basic Research, 2017, 254, 1600679.	0.7	5
39	Thermodynamic analysis of vapor-phase epitaxy of CdTe using a metallic Cd source. Journal of Crystal Growth, 2017, 470, 122-127.	0.7	2
40	Crystallization of semi-insulating HVPE-GaN with solid iron as a source of dopants. Journal of Crystal Growth, 2017, 475, 121-126.	0.7	13
41	1-kV vertical Ga2O3 field-plated Schottky barrier diodes. Applied Physics Letters, 2017, 110, .	1.5	421
42	Preparation of 2-in.-diameter (001) Î²-Ga2O3homoepitaxial wafers by halide vapor phase epitaxy. Japanese Journal of Applied Physics, 2017, 56, 110310.	0.8	26
43	Crystal growth of HVPE-GaN doped with germanium. Journal of Crystal Growth, 2017, 480, 102-107.	0.7	26
44	State-of-the-art technologies of gallium oxide power devices. Journal Physics D: Applied Physics, 2017, 50, 333002.	1.3	212
45	First demonstration of vertical Ga₂O₃ MOSFET: Planar structure with a current aperture. , 2017, , .		13
46	Direct Growth of CdTe on a (211) Si Substrate with Vapor Phase Epitaxy Using a Metallic Cd Source. Journal of Electronic Materials, 2017, 46, 5884-5888.	1.0	2
47	Thermal and chemical stabilities of group-III sesquioxides in a flow of either N₂ or H₂. Japanese Journal of Applied Physics, 2016, 55, 1202BE.	0.8	6
48	Temperature-dependent capacitanceâ€"voltage and currentâ€"voltage characteristics of Pt/Ga2O3 (001) Schottky barrier diodes fabricated on <i>n</i>â€"â€"Ga2O3 drift layers grown by halide vapor phase epitaxy. Applied Physics Letters, 2016, 108, .	1.5	268
49	Current status of Ga₂O₃ power devices. Japanese Journal of Applied Physics, 2016, 55, 1202A1.	0.8	188
50	Electronic properties of the residual donor in unintentionally doped Î²-Ga2O3. Journal of Applied Physics, 2016, 120, .	1.1	68
51	Investigation of NH3input partial pressure for N-polarity InGaN growth on GaN substrates by tri-halide vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FA01.	0.8	6
52	Influence of high-temperature processing on the surface properties of bulk AlN substrates. Journal of Crystal Growth, 2016, 446, 33-38.	0.7	12
53	Tri-halide vapor phase epitaxy of thick GaN using gaseous GaCl3 precursor. Journal of Crystal Growth, 2016, 456, 140-144.	0.7	17
54	Growth of thick and high crystalline quality InGaN layers on GaN (0001Â¯) substrate using tri-halide vapor phase epitaxy. Journal of Crystal Growth, 2016, 456, 145-150.	0.7	14

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55	Anisotropy, phonon modes, and free charge carrier parameters in monoclinic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Î²</mml:mi></mml:math>-gallium oxide single crystals. Physical Review B, 2016, 93, .	1.1	147
56	Ga2O3 field-plated schottky barrier diodes with a breakdown voltage of over 1 kV. , 2016, , .		2
57	Formation mechanism of AlN whiskers on sapphire surfaces heat-treated in a mixed flow of H2and N2. Japanese Journal of Applied Physics, 2016, 55, 05FF01.	0.8	1
58	Tri-halide vapor-phase epitaxy of GaN using GaCl₃ on polar, semipolar, and nonpolar substrates. Applied Physics Express, 2016, 9, 105501.	1.1	14
59	Recent progress in Ga₂O₃power devices. Semiconductor Science and Technology, 2016, 31, 034001.	1.0	783
60	Gallium Oxide Schottky Barrier Diodes. IEEJ Transactions on Electronics, Information and Systems, 2016, 136, 479-483.	0.1	0
61	Current Status of Gallium Oxide-Based Power Device Technology. , 2015, , .		3
62	High rate InN growth by two-step precursor generation hydride vapor phase epitaxy. Journal of Crystal Growth, 2015, 422, 15-19.	0.7	7
63	Thermal stability of Î²-Ga₂O₃in mixed flows of H₂and N₂. Japanese Journal of Applied Physics, 2015, 54, 041102.	0.8	38
64	Ga<inf>2</inf>O<inf>3</inf> Schottky barrier diodes with n[−]-Ga<inf>2</inf>O<inf>3</inf> drift layers grown by HVPE. , 2015, , .		23
65	Homoepitaxial growth of Î²-Ga₂O₃layers by halide vapor phase epitaxy. Applied Physics Express, 2015, 8, 015503.	1.1	288
66	Growth of thick InGaN layers by tri-halide vapor phase epitaxy. Japanese Journal of Applied Physics, 2014, 53, 05FL02.	0.8	28
67	Thermodynamic study of Î²-Ga2O3 growth by halide vapor phase epitaxy. Journal of Crystal Growth, 2014, 405, 19-22.	0.7	100
68	Effects of substrate nitridation and buffer layer on the crystalline improvements of semi-polar InN(101Â¯3) crystal on GaAs(110) by MOVPE. Journal of Crystal Growth, 2013, 367, 122-125.	0.7	2
69	Suppression of twin formation for the growth of InN(10-1-3) on GaAs(110) by metalorganic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 472-475.	0.8	1
70	Effect of High NH3Input Partial Pressure on Hydride Vapor Phase Epitaxy of InN Using Nitrided (0001) Sapphire Substrates. Japanese Journal of Applied Physics, 2013, 52, 08JD05.	0.8	1
71	High-Temperature Heat-Treatment ofc-,a-,r-, andm-Plane Sapphire Substrates in Mixed Gases of H2and N2. Japanese Journal of Applied Physics, 2013, 52, 08JB10.	0.8	8
72	Thermodynamic analysis of InGaN-HVPE growth using group-III chlorides, bromides, and iodides. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 413-416.	0.8	6

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73	Structural and Optical Properties of Carbon-Doped AlN Substrates Grown by Hydride Vapor Phase Epitaxy Using AlN Substrates Prepared by Physical Vapor Transport. Applied Physics Express, 2012, 5, 125501.	1.1	45
74	Preparation of a Freestanding AlN Substrate from a Thick AlN Layer Grown by Hydride Vapor Phase Epitaxy on a Bulk AlN Substrate Prepared by Physical Vapor Transport. Applied Physics Express, 2012, 5, 055504.	1.1	121
75	Influence of source gas supply sequence on hydride vapor phase epitaxy of AlN on (0001) sapphire substrates. Journal of Crystal Growth, 2012, 360, 197-200.	0.7	7
76	Formation of AlN on sapphire surfaces by high-temperature heating in a mixed flow of H2 and N2. Journal of Crystal Growth, 2012, 350, 60-65.	0.7	11
77	Influence of growth temperature on the twin formation of InN{10$ ar 1 $3} on GaAs(110) by metalorganic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 677-680.	0.8	0
78	Carrier Gas Dependence at Initial Processes fora-Plane AlN Growth onr-Plane Sapphire Substrates by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 055501.	0.8	2
79	Growth of semi-polar InN layer on GaAs (1 1 0) surface by MOVPE. Journal of Crystal Growth, 2011, 318, 479-482.	0.7	4
80	Theoretical study on the influence of surface hydrogen coverage on the initial growth process of AlN(0001) surfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1577-1580.	0.8	2
81	First-principles study on the effect of surface hydrogen coverage on the adsorption process of ammonia on InN(0001) surfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2267-2269.	0.8	3
82	Triâ€halide vapor phase epitaxy of GaN using GaCl₃ gas as a group III precursor. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1471-1474.	0.8	13
83	Semi-polar InN(10$ ar 1 $3) dominant growth on GaAs(110) substrate by mixing hydrogen in carrier gas. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2025-2027.	0.8	2
84	Control of in-plane epitaxial relationship of c -plane AlN layers grown on a -plane sapphire substrates by hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2028-2030.	0.8	16
85	Thermodynamic analysis on HVPE growth of InGaN ternary alloy. Journal of Crystal Growth, 2011, 318, 441-445.	0.7	15
86	Two-Step Growth of (0001) ZnO Single-Crystal Layers on (0001) Sapphire Substrates by Halide Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 125503.	0.8	2
87	Carrier Gas Dependence at Initial Processes fora-Plane AlN Growth onr-Plane Sapphire Substrates by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 055501.	0.8	10
88	Two-Step Growth of (0001) ZnO Single-Crystal Layers on (0001) Sapphire Substrates by Halide Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 125503.	0.8	0
89	Influence of substrate polarity of (0 0 0 1) and (0 0 01Â¯)GaN surfaces on hydride vapor-phase epitaxy of InN. Journal of Crystal Growth, 2010, 312, 651-655.	0.7	3
90	Investigation of void formation beneath thin AlN layers by decomposition of sapphire substrates for self-separation of thick AlN layers grown by HVPE. Journal of Crystal Growth, 2010, 312, 2530-2536.	0.7	45

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91	Selective growth of InN on patterned GaAs(111)B substrate - influence of InN decomposition at the interface. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2019-2021.	0.8	4
92	Temperature dependence of InN growth on (0001) sapphire substrates by atmospheric pressure hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2022-2024.	0.8	7
93	Theoretical investigation of the decomposition mechanism of AlN(0001) surface under a hydrogen atmosphere. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2265-2267.	0.8	3
94	<i>In situ</i>Gravimetric Monitoring of Thermal Decomposition and Hydrogen Etching Rates of 6H-SiC(0001) Si Face. Japanese Journal of Applied Physics, 2009, 48, 095505.	0.8	5
95	<i>Ab initio</i> calculation for an initial growth process of GaN on (0001) and (000$ ar 1 $) surfaces by vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S301.	0.8	6
96	Controlled formation of voids at the AlN/sapphire interface by sapphire decomposition for selfâ€separation of the AlN layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S447.	0.8	3
97	Investigation of polarity dependent InN{0001} decomposition in N₂ and H₂ ambient. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S372.	0.8	16
98	Preparation of a crack-free AlN template layer on sapphire substrate by hydride vapor-phase epitaxy at 1450Â°C. Journal of Crystal Growth, 2009, 311, 2837-2839.	0.7	19
99	In situ gravimetric monitoring of surface reactions between sapphire and NH3. Journal of Crystal Growth, 2009, 311, 3110-3113.	0.7	7
100	Theoretical investigation on the decomposition process of GaN(0001) surface under a hydrogen atmosphere. Journal of Crystal Growth, 2009, 311, 3103-3105.	0.7	6
101	Characterization of a freestanding AlN substrate prepared by hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1512-1514.	0.8	9
102	Growth of thin protective AlN layers on sapphire substrates at 1065 Â°C for hydride vapor phase epitaxy of AlN above 1300 Â°C. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1515-1517.	0.8	18
103	Experimental and <i>abâ€initio</i> studies of temperature dependent InN decomposition in various ambient. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1518-1521.	0.8	14
104	First principles study of the decomposition processes of AlN in a hydrogen atmosphere. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3042-3044.	0.8	2
105	Polarities of AlN films and underlying 3C-SiC intermediate layers grown on (111) Si substrates. Journal of Crystal Growth, 2008, 310, 96-100.	0.7	22
106	Influence of hydrogen input partial pressure on the polarity of InN on GaAs (111)A grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2008, 310, 1602-1606.	0.7	5
107	Ab initio calculation for the decomposition process of GaN (0001) and (0001Â¯) surfaces. Journal of Crystal Growth, 2008, 310, 1632-1636.	0.7	12
108	High-temperature growth of thick AlN layers on sapphire (0 0 0 1) substrates by solid source halide vapor-phase epitaxy. Journal of Crystal Growth, 2008, 310, 4016-4019.	0.7	31

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109	Improvements in the crystalline quality of MOVPE-InN layers by facet controlling with hydrogen partial pressure. Journal of Crystal Growth, 2008, 310, 4954-4958.	0.7	5
110	In situGravimetric Monitoring of Decomposition Rate on Surface of (10ar12)R-Plane Sapphire for High-Temperature Growth of Nonpolar AlN. Japanese Journal of Applied Physics, 2008, 47, 3434-3437.	0.8	17
111	Hydride vapor-phase epitaxy of AlN and AlGaN. Acta Crystallographica Section A: Foundations and Advances, 2008, 64, C87-C88.	0.3	0
112	Study of the Decomposition Processes of (0001)AlN in a Hydrogen Atmosphere. Japanese Journal of Applied Physics, 2007, 46, L1114-L1116.	0.8	8
113	Theoretical Analysis for Surface Reconstruction of AlN and InN in the Presence of Hydrogen. Japanese Journal of Applied Physics, 2007, 46, 5112.	0.8	27
114	MOVPE-like HVPE of AlN using solid aluminum trichloride source. Journal of Crystal Growth, 2007, 298, 332-335.	0.7	11
115	Influence of surface atom arrangement on the growth of InN layers on GaAs (111)A and (111)B surfaces by metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 2007, 298, 387-389.	0.7	5
116	Hydride vapor phase epitaxy of InN by the formation of InCl3 using In metal and Cl2. Journal of Crystal Growth, 2007, 300, 57-61.	0.7	24
117	Growth of thick AlxGa1â˜xN ternary alloy by hydride vapor-phase epitaxy. Journal of Crystal Growth, 2007, 300, 164-167.	0.7	11
118	Al- and N-polar AlN layers grown on c-plane sapphire substrates by modified flow-modulation MOCVD. Journal of Crystal Growth, 2007, 305, 360-365.	0.7	65
119	Polarity dependence of AlN {0001} decomposition in flowing H2. Journal of Crystal Growth, 2007, 305, 366-371.	0.7	61
120	HVPE growth of AlxGa1â˜xN ternary alloy using AlCl3 and GaCl. Journal of Crystal Growth, 2007, 305, 335-339.	0.7	20
121	A new system for growing thick InN layers by hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2419-2422.	0.8	5
122	In situ gravimetric monitoring of decomposition rate on the surface of (0001) c-plane sapphire for the high temperature growth of AlN. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2297-2300.	0.8	24
123	First-principles calculation and X-ray absorption fine structure analysis of Fe doping mechanism for semi-insulating GaN growth on GaAs substrates. Physica Status Solidi (B): Basic Research, 2007, 244, 1862-1866.	0.7	1
124	Thermodynamic Analysis of Various Types of Hydride Vapor Phase Epitaxy System for High-Speed Growth of InN. Japanese Journal of Applied Physics, 2006, 45, L1203-L1205.	0.8	2
125	Thermodynamic study on the role of hydrogen during hydride vapor phase epitaxy of Alx Ga1â€“xN. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1457-1460.	0.8	5
126	Thermodynamics on hydride vapor phase epitaxy of AlN using AlCl3 and NH3. Physica Status Solidi (B): Basic Research, 2006, 243, 1431-1435.	0.7	19

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127	Fe-doped semi-insulating GaN substrates prepared by hydride vapor-phase epitaxy using GaAs starting substrates. Journal of Crystal Growth, 2006, 296, 11-14.	0.7	16
128	Growth of GaN Directly on Si(111) Substrate by Controlling Atomic Configuration of Si Surface by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2006, 45, L478-L481.	0.8	20
129	Impact of crystallization manner of the buffer layer on the crystalline quality of GaN epitaxial layers on GaAs (111)A substrate. Journal of Crystal Growth, 2005, 275, e1149-e1154.	0.7	5
130	Growth and characterization of thick GaN layers with high Fe doping. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2058-2061.	0.8	5
131	Growth of thick AlN layer on sapphire (0001) substrate using hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2062-2065.	0.8	13
132	Fabrication of Semi-Insulating GaN Wafers by Hydride Vapor Phase Epitaxy of Fe-Doped Thick GaN Layers Using GaAs Starting Substrates. Japanese Journal of Applied Physics, 2005, 44, L1519-L1521.	0.8	3
133	Growth of Fe-Doped Thick GaN Layers for Preparation of Semi-Insulating GaN Substrates. Japanese Journal of Applied Physics, 2005, 44, L1072-L1075.	0.8	9
134	Trade-off between thickness and temperature ramping rate of GaN buffer layer studied for high quality GaN growth on GaAs (111)A substrate. Journal of Crystal Growth, 2004, 268, 1-7.	0.7	4
135	Influence of substrate polarity on the low-temperature GaN buffer layer growth on GaAs (111)A and (111)B surfaces. Journal of Crystal Growth, 2003, 247, 245-250.	0.7	13
136	Hydride vapor phase epitaxy of AlN: thermodynamic analysis of aluminum source and its application to growth. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2498-2501.	0.8	68
137	Improvements in crystalline quality of thick GaN layers on GaAs (111)A by periodic insertion of low-temperature GaN buffer layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2141-2144.	0.8	0
138	Influence of Temperature Ramping Rate on Thick GaN Growth on GaAs (111)A Surfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 166-169.	0.8	0
139	High Temperature Ramping Rate for GaAs (111)A Substrate Covered with a Thin GaN Buffer Layer for Thick GaN Growth at 1000Â°C. Japanese Journal of Applied Physics, 2003, 42, L526-L528.	0.8	3
140	Vinyltitanium as an initiator for the polymerization of acetylene. Journal of Polymer Science Part A, 2002, 40, 2663-2669.	2.5	4
141	Thick and high-quality GaN growth on GaAs (111) substrates for preparation of freestanding GaN. Journal of Crystal Growth, 2002, 246, 215-222.	0.7	24
142	Growth of Thick Hexagonal GaN Layer on GaAs (111)A Surfaces for Freestanding GaN by Metalorganic Hydrogen Chloride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2000, 39, L703-L706.	0.8	26
143	Self-Separation of a Thick AlN Layer from a Sapphire Substrate via Interfacial Voids Formed by the Decomposition of Sapphire. Applied Physics Express, 0, 1, 045003.	1.1	36